

50 V, 170 mA dual P-channel Trench MOSFET Rev. 1 — 19 May 2011

Product data sheet

Product profile 1.

1.1 General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in an ultra small and flat lead SOT666 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver

- ESD protection up to 1 kV
- AEC-Q101 qualified
- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
V _{DS}	drain-source voltage	T _j = 25 °C	-	-	-50	V
V _{GS}	gate-source voltage		-20	-	20	V
I _D	drain current	V_{GS} = -10 V; T_{amb} = 25 °C	<u>[1]</u> _	-	-170	mA
Static cha	racteristics (per transisto	or)				
R _{DSon}	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = -10 \ V; \ I_D = -100 \ mA; \\ T_j = 25 \ ^\circ C \end{array}$	-	4.5	7.5	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

nexperia

50 V, 170 mA dual P-channel Trench MOSFET

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source 1		24 - 22
2	G1	gate 1		
3	D2	drain 2		
4	S2	source 2	0	G1 + F F F G2
5	G2	gate 2		
6	D1	drain 1	SOT666 (SOT666)	S1 S2 sym147

3. Ordering information

Table 3. Or	dering information		
Type number	Package		
	Name	Description	Version
BSS84AKV	SOT666	plastic surface-mounted package; 6 leads	SOT666

4. Marking

Table 4.	Marking codes	
----------	---------------	--

Type number	Marking code ^[1]
BSS84AKV	EG

[1] % = placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transi	istor					
V _{DS}	drain-source voltage	T _j = 25 °C		-	-50	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	$V_{GS} = -10 \text{ V}; \text{ T}_{amb} = 25 \text{ °C}$	<u>[1]</u>	-	-170	mA
		$V_{GS} = -10 \text{ V}; \text{ T}_{amb} = 100 \text{ °C}$	<u>[1]</u>	-	-110	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-0.7	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	330	mW
			<u>[1]</u>	-	390	mW
		T _{sp} = 25 °C		-	1090	mW
Per devic	e					
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	500	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-d	rain diode					
I _S	source current	T _{amb} = 25 °C	<u>[1]</u>	-	-170	mA
ESD max	imum rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	1000	V

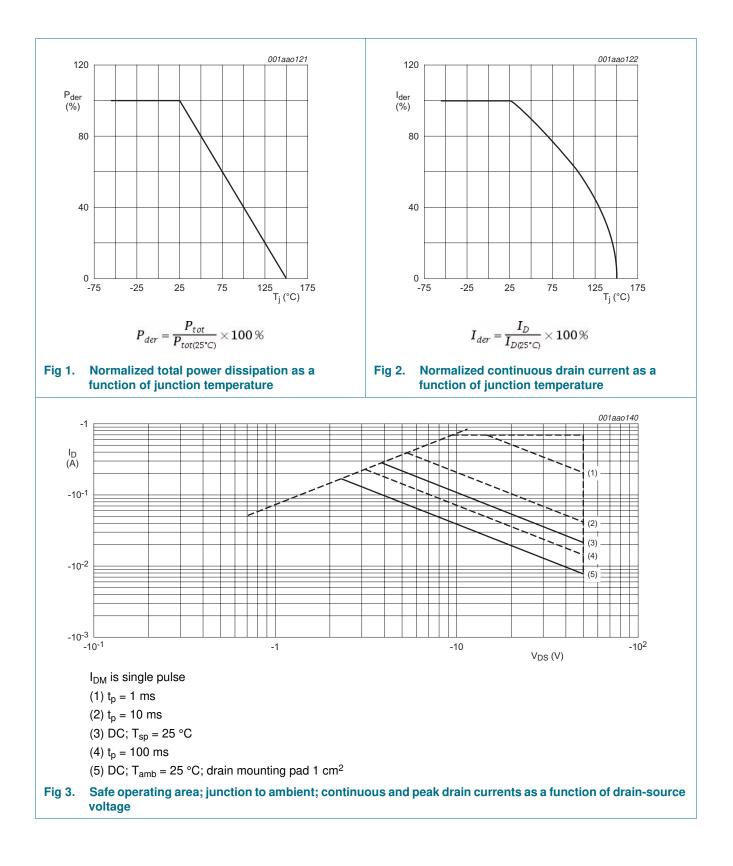
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

BSS84AKV

50 V, 170 mA dual P-channel Trench MOSFET



Product data sheet

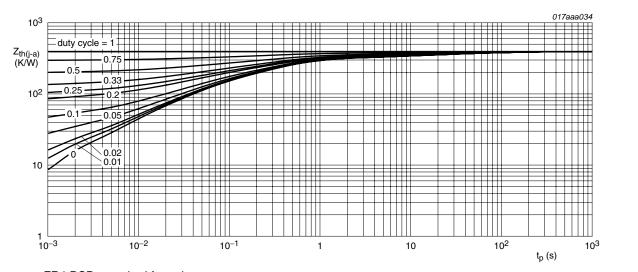
6. Thermal characteristics

	nermai characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device							
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	-	250	K/W
Per transisto	or						
R _{th(j-a)}	thermal resistance from junction to	in free air	[1]	-	330	380	K/W
	ambient		[2]	-	280	320	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solde point	er		-	-	115	K/W

Table 6. Thermal characteristics

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

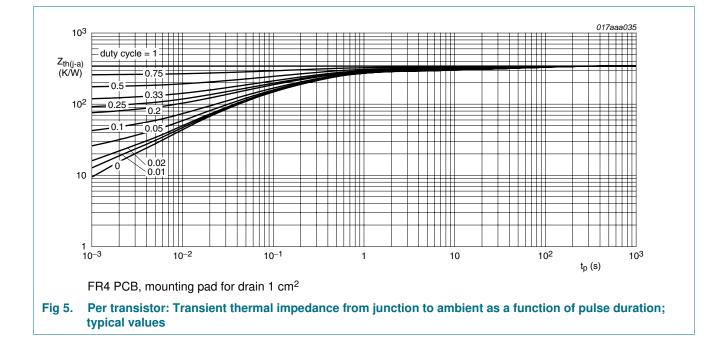


FR4 PCB, standard footprint

Fig 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

BSS84AKV

50 V, 170 mA dual P-channel Trench MOSFET

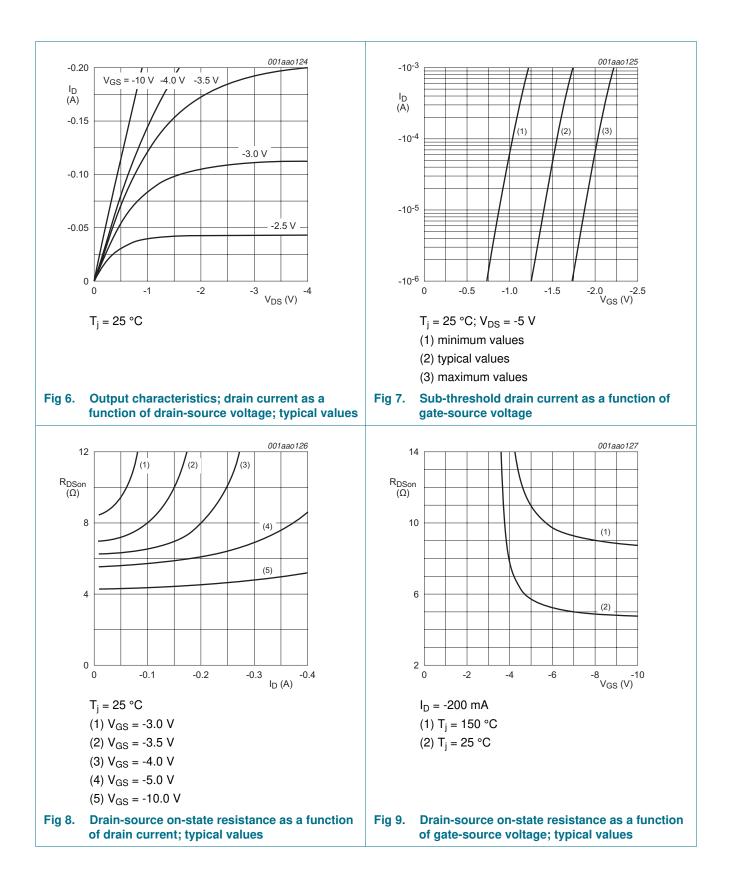


7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	racteristics (per transistor)					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -10 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	-50	-	-	V
V _{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^\circ\text{C}$	-1.1	-1.6	-2.1	V
I _{DSS}	drain leakage current	$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μA
		$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-2	μA
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-10	μA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μA
R _{DSon}	drain-source on-state	V_{GS} = -10 V; I_D = -100 mA; T_j = 25 °C	-	4.5	7.5	Ω
	resistance	V_{GS} = -10 V; I_{D} = -100 mA; T_{j} = 150 °C	-	8	13.5	Ω
		V_{GS} = -5 V; I_D = -100 mA; T_j = 25 °C	-	5.7	8.5	Ω
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_{D} = -100 mA; T_{j} = 25 °C	-	150	-	mS
Dynamic of	characteristics (per transistor	r)				
Q _{G(tot)}	total gate charge	V_{DS} = -25 V; I_{D} = -200 mA; V_{GS} = -5 V;	-	0.26	0.35	nC
Q _{GS}	gate-source charge	$T_j = 25 \ ^{\circ}C$	-	0.12	-	nC
Q _{GD}	gate-drain charge		-	0.09	-	nC
C _{iss}	input capacitance	$V_{DS} = -25 V$; f = 1 MHz; $V_{GS} = 0 V$;	-	24	36	pF
C _{oss}	output capacitance	$T_j = 25 \ ^{\circ}C$	-	4.5	-	pF
C _{rss}	reverse transfer capacitance		-	1.3	-	pF
t _{d(on)}	turn-on delay time	$V_{DS}=-30~V;~R_L=250~\Omega;~V_{GS}=-10~V;$	-	13	26	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	11	-	ns
t _{d(off)}	turn-off delay time		-	48	96	ns
t _f	fall time		-	25	-	ns
Source-dr	ain diode (per transistor)					
V _{SD}	source-drain voltage	I _S = -115 mA; V _{GS} = 0 V; T _i = 25 °C	-0.48	-0.85	-1.2	V

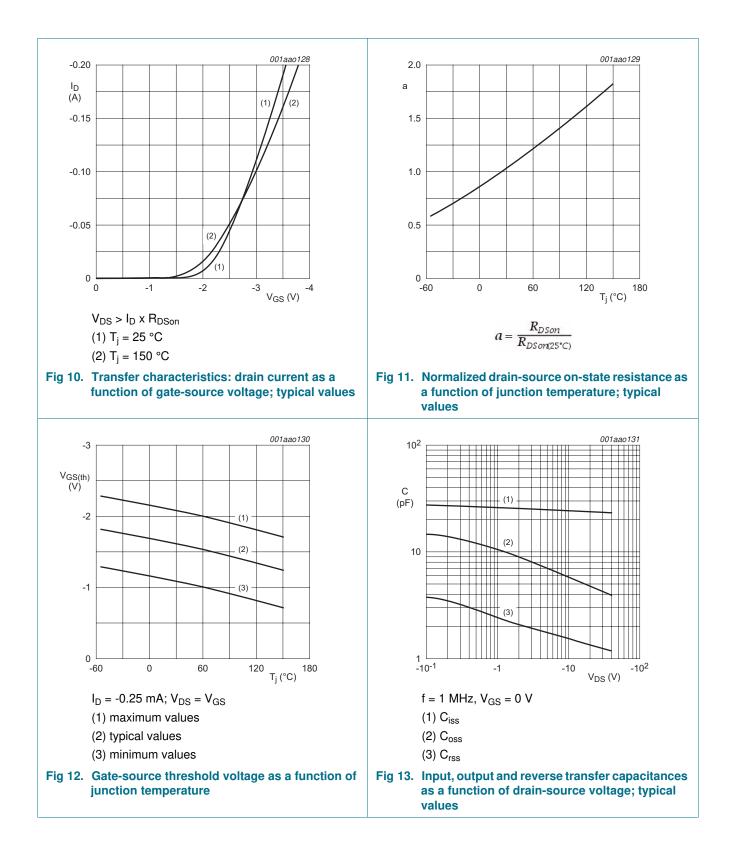
BSS84AKV

50 V, 170 mA dual P-channel Trench MOSFET



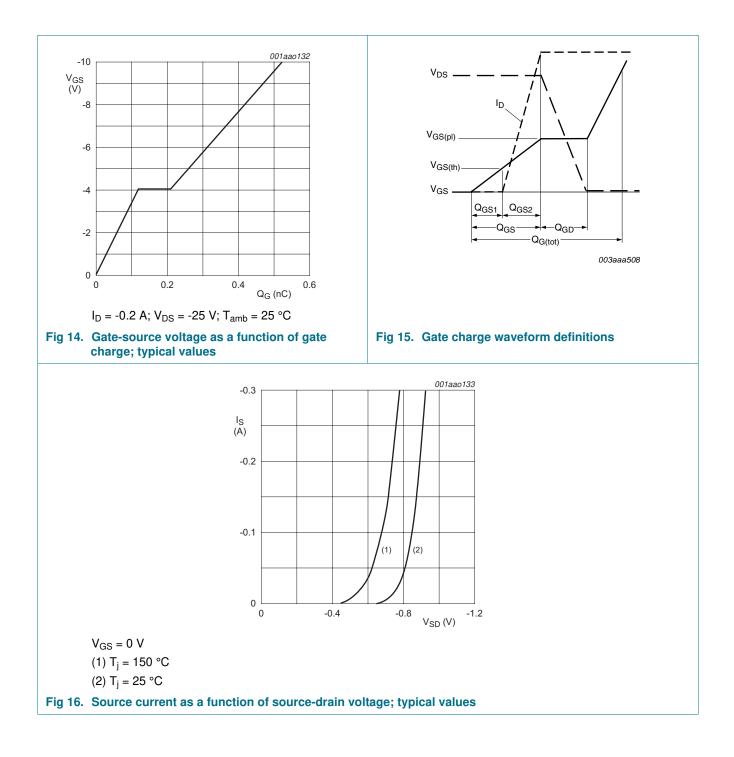
BSS84AKV

50 V, 170 mA dual P-channel Trench MOSFET



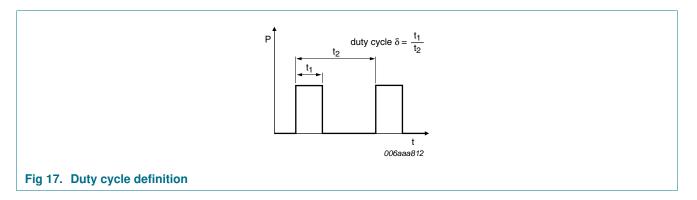
BSS84AKV

50 V, 170 mA dual P-channel Trench MOSFET



50 V, 170 mA dual P-channel Trench MOSFET

8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

50 V, 170 mA dual P-channel Trench MOSFET

9. Package outline

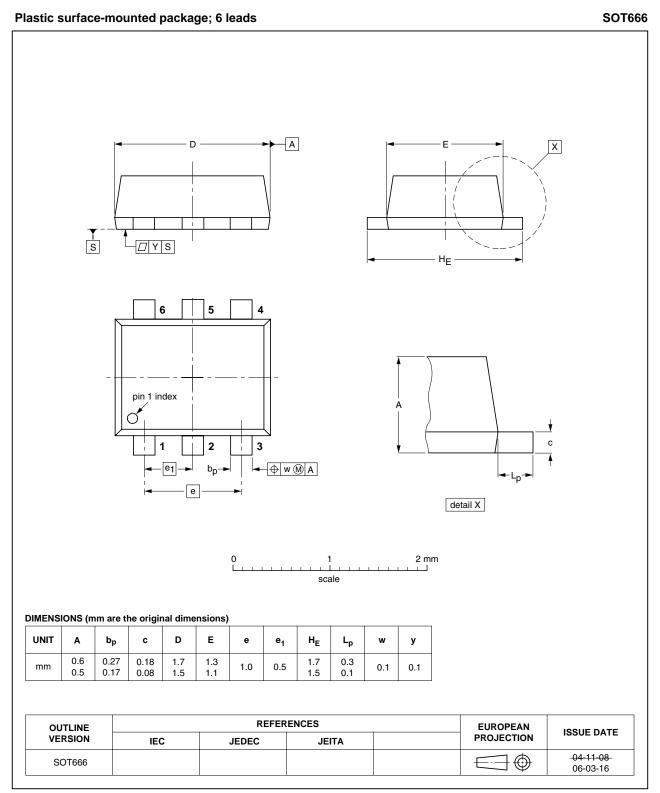
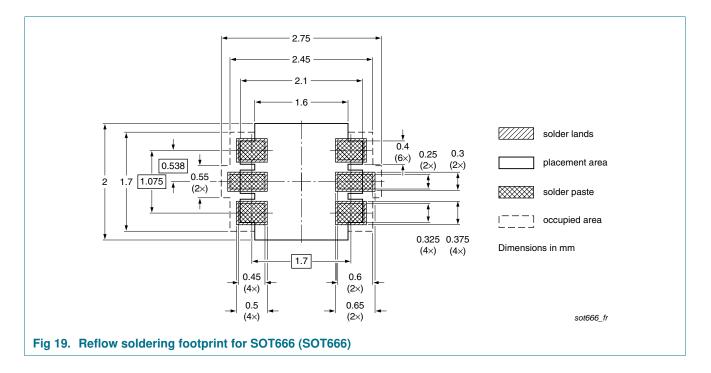


Fig 18. Package outline SOT666 (SOT666)

All information provided in this document is subject to legal disclaimers.

50 V, 170 mA dual P-channel Trench MOSFET

10. Soldering



11. Revision history

Table 8.	Revision hi	story			
Document	ID	Release date	Data sheet status	Change notice	Supersedes
BSS84AKV	v.1	20110519	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia</u>.com.

12.2 Definitions

Preview — The document is a preview version only. The document is still subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Nexperia and its customer, unless Nexperia and

customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Nexperia product is deemed to offer functions and qualities beyond those described in the Product data sheet.

12.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Nexperia does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall Nexperia be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Nexperia's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Nexperia.

Right to make changes — Nexperia reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Nexperia products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of a Nexperia product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Nexperia accepts no liability for inclusion and/or use of Nexperia products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Nexperia makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Nexperia products, and Nexperia accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Nexperia product suble and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Nexperia does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Nexperia products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). Nexperia does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

50 V, 170 mA dual P-channel Trench MOSFET

Terms and conditions of commercial sale — Nexperia products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nexperia.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Nexperia hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Nexperia products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

13. Contact information

For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: <u>salesaddresses@nexperia.com</u>

12.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

50 V, 170 mA dual P-channel Trench MOSFET

14. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Marking
5	Limiting values
6	Thermal characteristics5
7	Characteristics7
8	Test information11
8.1	Quality information11
9	Package outline12
10	Soldering
11	Revision history14
12	Legal information15
101	5 · · · · · · · · · · · · · · · · · · ·
12.1	Data sheet status
12.1 12.2	Data sheet status
12.2	Definitions15